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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	24	microcrystalline and MOS and polysilicon and floating and control and gate and nitride and gas and reaction and insulating and material	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 10:59
L2	24	microcrystalline and MOS and polysilicon and floating and control and gate and nitride and gas and reaction and insulating and material and amorphous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 11:03
L3	24	2 and (thermal or thremally or treat or treating or amorphous or microcrystalline or material or reaction or gas or grain or size or "50" or "300" or nitride or polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 11:05
L4	24	2 and (thermal or thremally or treat or treating or amorphous or microcrystalline or material or reaction or gas or grain or size or "50" or "300" or nitride or polysilicon or memory or cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 11:16
L5	2	4 and bit and lines and plurality and thermal and amorphous and microcrystalline and material	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 11:14
L6	24	2 and (thermal or thremally or treat or treating or amorphous or microcrystalline or material or reaction or gas or grain or size or "50" or "300" or nitride or polysilicon or memory or cell or angstroms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 11:16